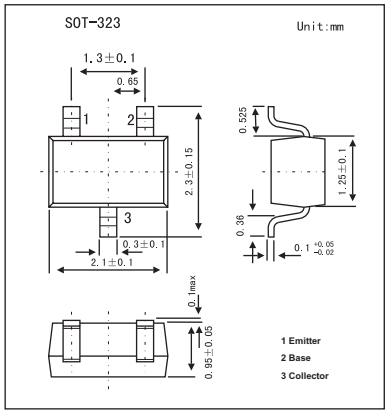
PNP General Purpose Transistor

2PA1576



Features

- Low current (max. 100 mA)
- Low voltage (max. 40 V).
- Low collector capacitance (typ. 2.5 pF).

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Peak collector current	I_{CM}	-200	mA
Peak base current	I_{BM}	-200	mA
Total power dissipation	P_{tot}	200	mW
Storage temperature	T_{stg}	-65 to +150	℃
Junction temperature	T_j	150	℃
Operating ambient temperature	T_{amb}	-65 to +150	℃
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	625	K/W

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	I_E = 0; V_{CB} = -30 V			-100	nA
		I_E = 0; V_{CB} = -30 V; T_j = 150 ℃			-5	μA
Emitter cut-off current	I_{EBO}	I_C = 0; V_{EB} = -4 V			-100	nA
DC current gain 2PA1576Q 2PA1576R 2PA1576S	h_{FE}	I_C = -1 mA; V_{CE} = -6 V	 120 180 270		 270 390 560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -50 mA; I_B = -5 mA; *			-500	mV
Collector capacitance	C_c	I_E = ie = 0; V_{CB} = -12 V; f = 1 MHz		2.5	3.5	pF
Transition frequency	f_T	I_C = -2 mA; V_{CE} = -12 V; f = 100 MHz	100			MHz

* Pulse test: tp ⩽ 300 μs; δ⩽ 0.02.

h_{FE} Classification

TYPE	2PA1576Q	2PA1576R	2PA1576S
Marking	FQ	FR	FS